

SANYO	No.4112	2SK1740
		N-Channel Junction Silicon FET HF amplifiers low frequency amplifiers analog switches

Features

- Adoption of FBET process.
- Large $|Y_{fs}|$.
- Small Ciss.
- Small-sized package permitting 2SK1740-applied sets to be made small and slim.

Absolute Maximum Ratings at Ta=25°C

			unit
Drain to Source Voltage	V_{DSX}	40	V
Gate to Drain Voltage	V_{GDS}	-40	V
Gate Current	I_G	10	mA
Drain Current	I_D	75	mA
Allowable Power Dissipation	P_D	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
G-D Breakdown Voltage	$V_{(BR)GDS}$	$I_G = -10\mu A, V_{DS} = 0$	-40			V
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = -20V, V_{DS} = 0$			-1.0	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 100\mu A$	-2.0	-3.0	-5.0	V
Drain Current	I_{DSS}^*	$V_{DS} = 10V, V_{GS} = 0$	40*		75*	mA
Forward Transfer Admittance	$ Y_{fs} $	(1) $V_{DS} = 10V, I_D = 10mA, f = 1kHz$	10	15		mS
		(2) $V_{DS} = 10V, V_{GS} = 0, f = 1kHz$	22	30		mS
Input Capacitance	Ciss	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		11		pF
Reverse Transfer Capacitance	Crss	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		2.5		pF
Noise Figure	NF	$V_{DS} = 10V, R_g = 1k\Omega, I_D = 1mA, f = 1kHz$		1.5		dB
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 10mA, V_{GS} = 0$		30		Ω

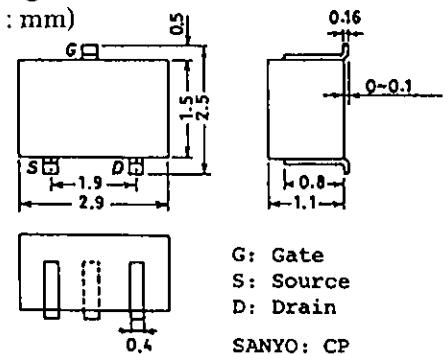
* : Pulse Test Pulse Width $\leq 2ms$

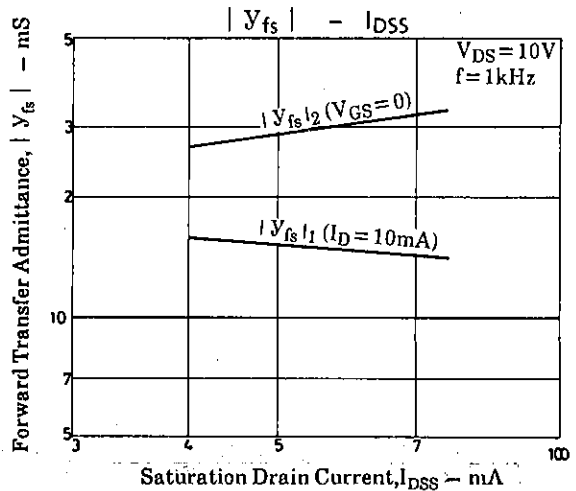
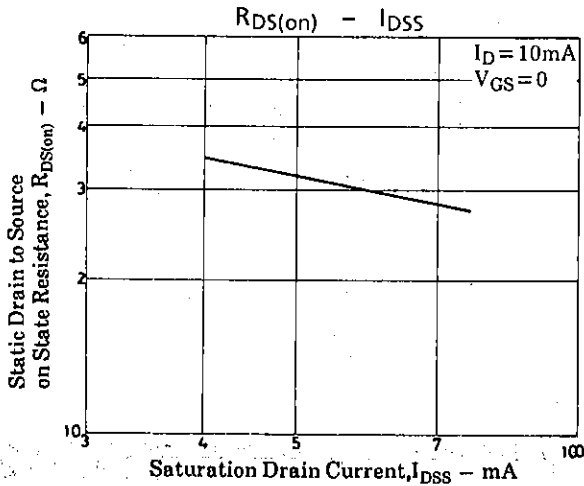
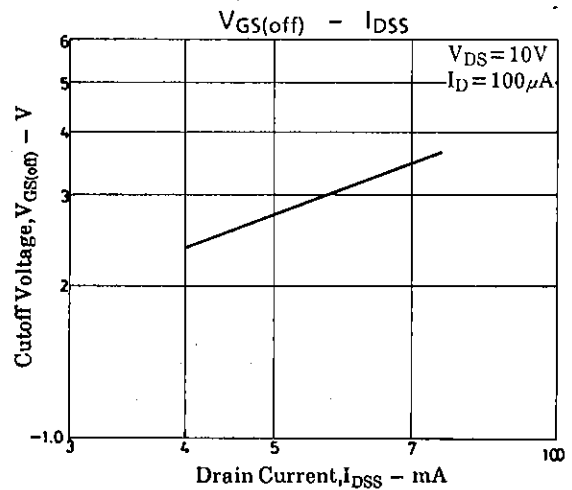
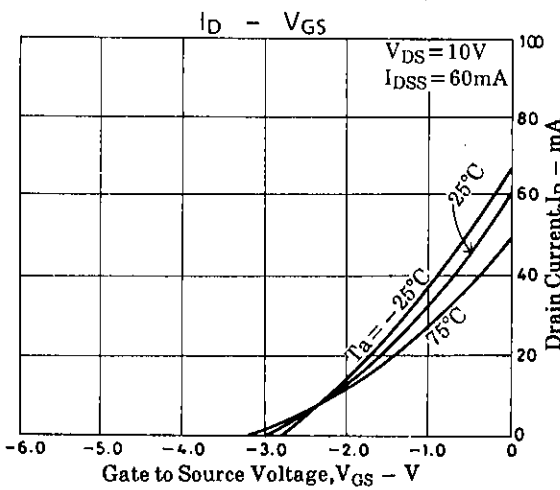
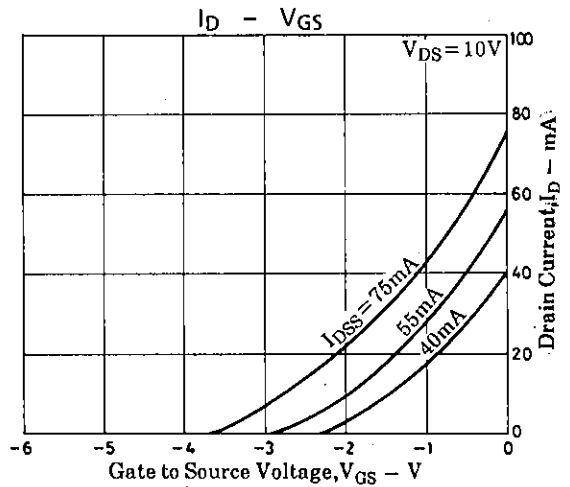
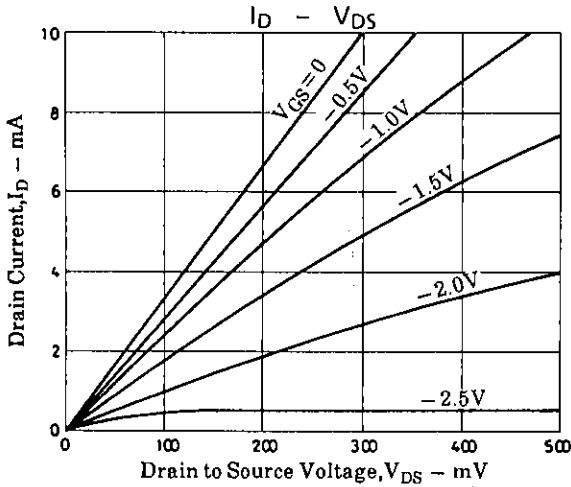
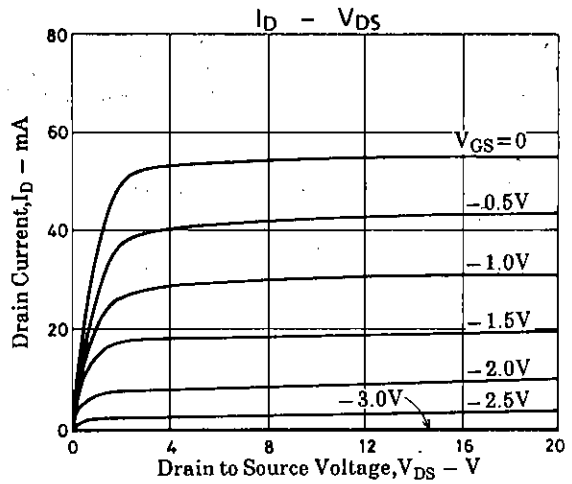
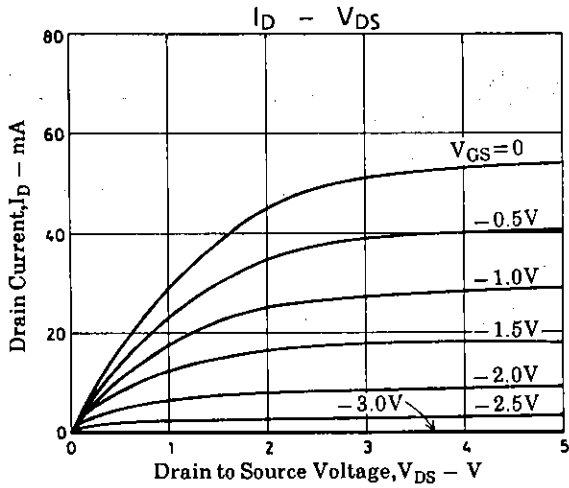
※ : The 2SK1740 is classified by I_{DSS} as follows (unit : mA)

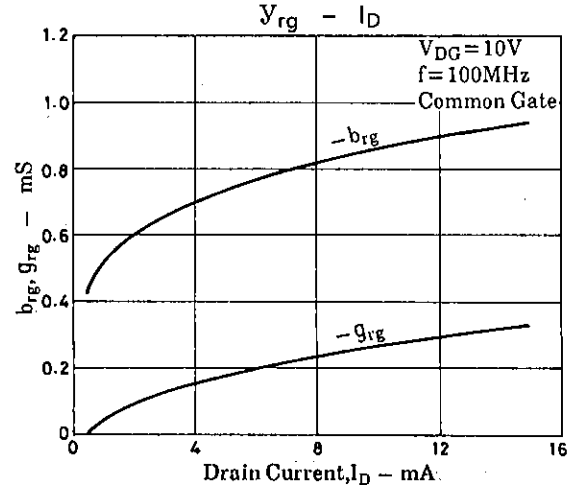
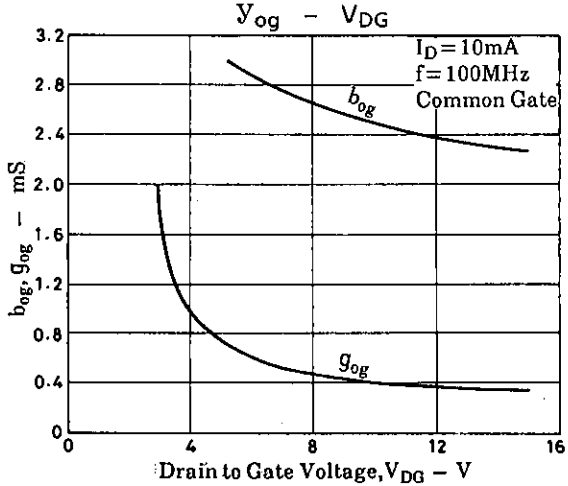
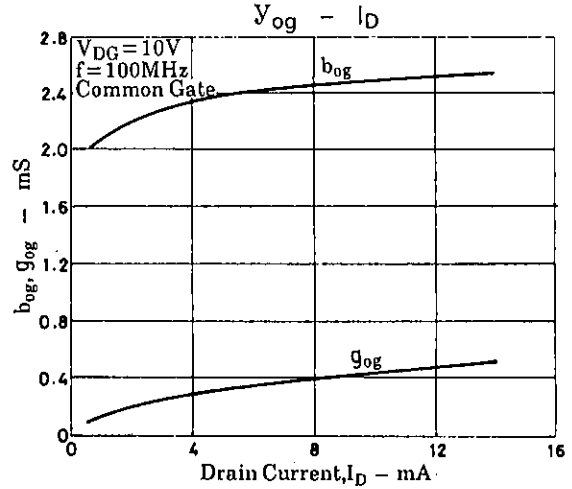
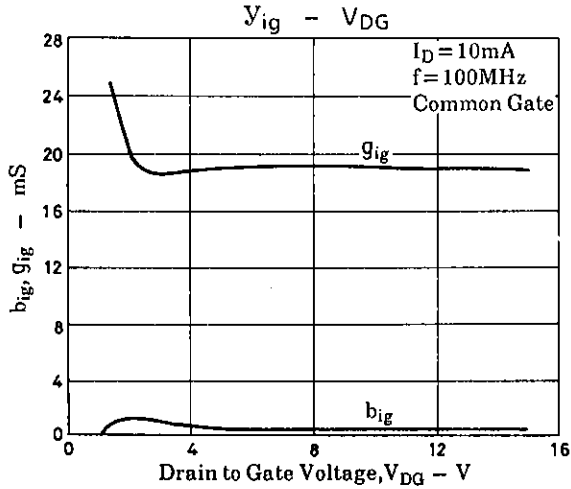
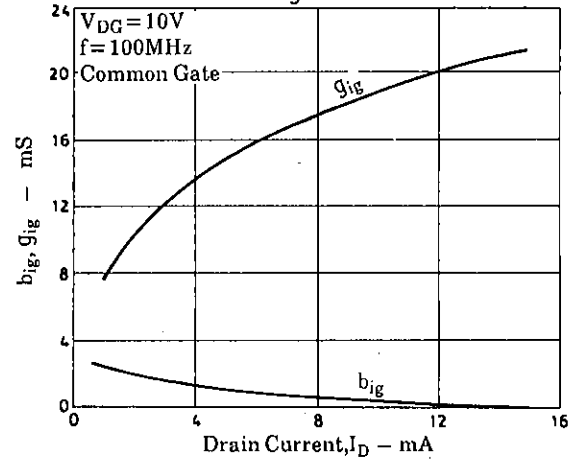
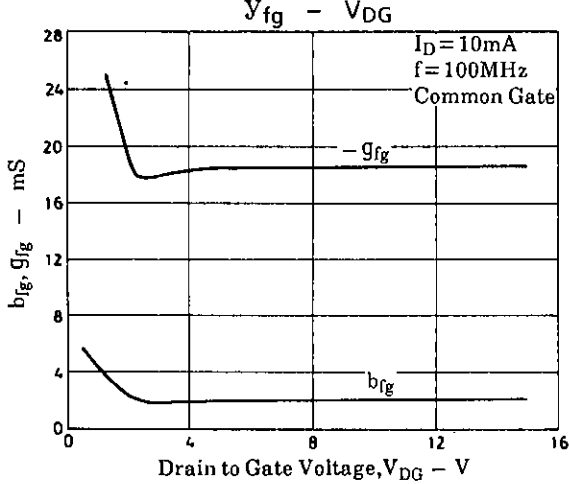
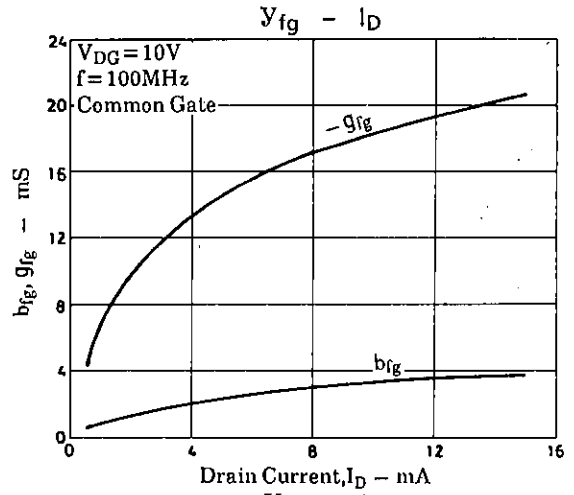
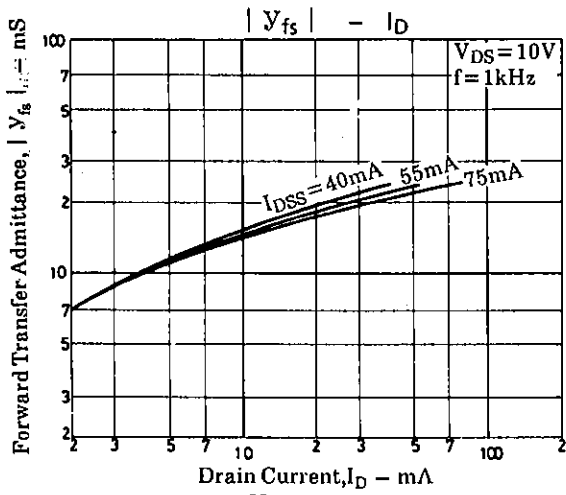
40	3	52	48	4	63	57	5	75
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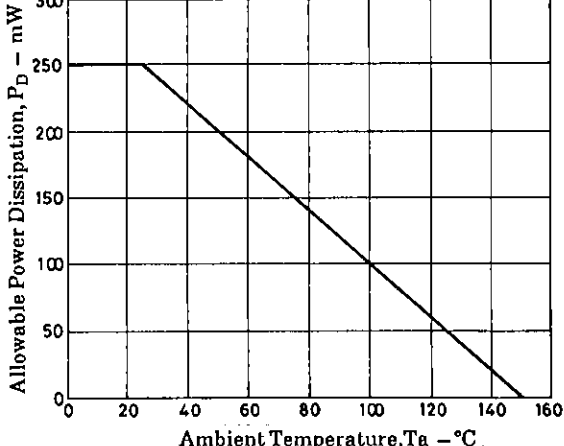
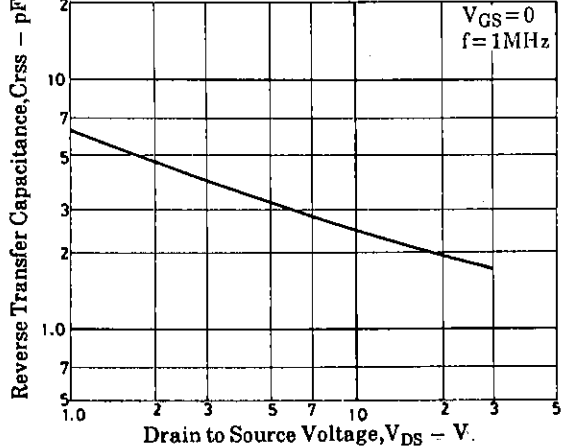
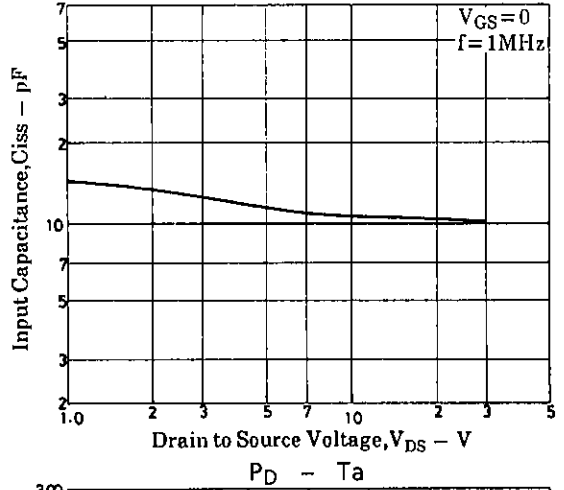
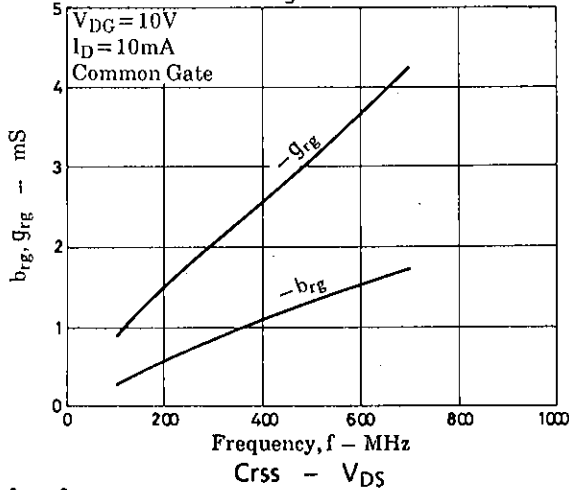
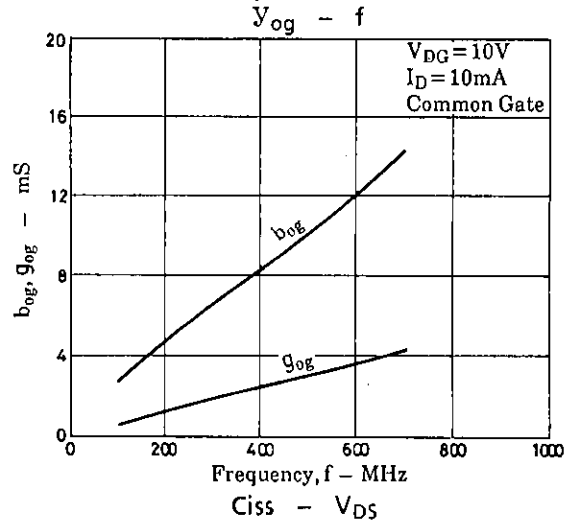
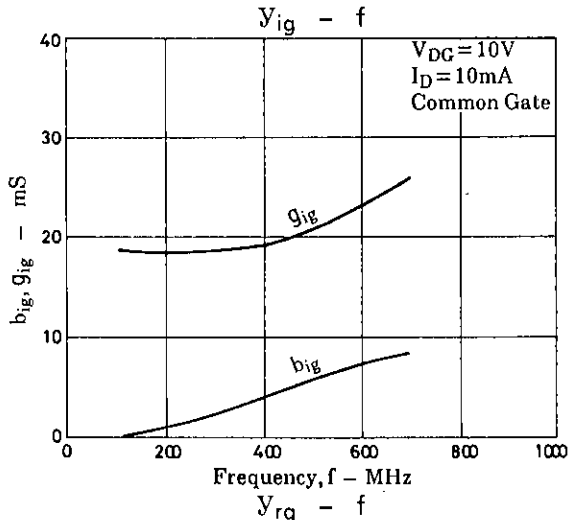
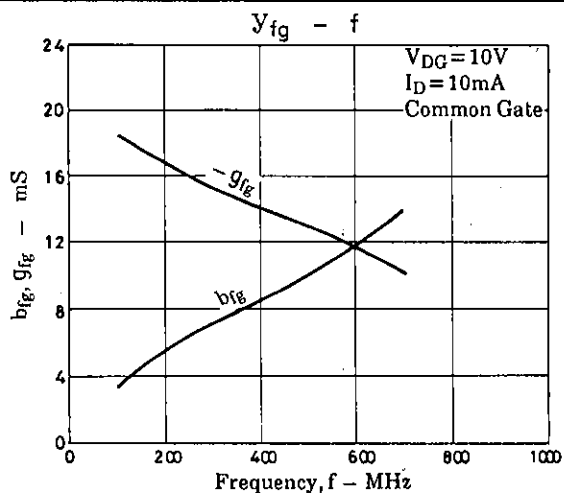
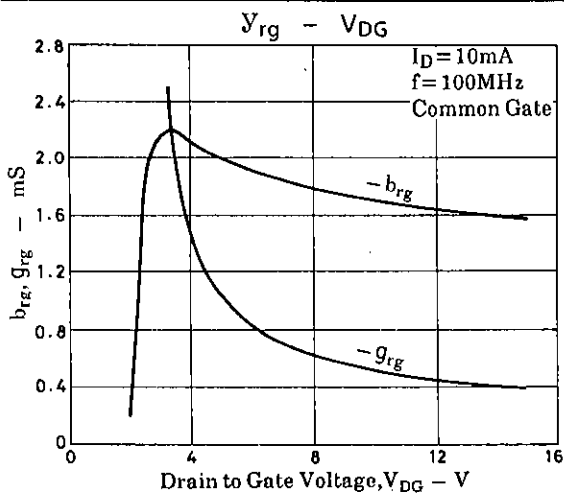
Marking : IJ
 I_{DSS} rank : 3,4,5

Package Dimensions 2050
(unit : mm)









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